

# Brudnyi Pavel

Russia, Tomsk

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Date of birth: 4th May 1994



## EDUCATION

### Tomsk State University (TSU)

QS Global World Ranking #=277

- PhD in Semiconductor Physics  
Department of Semiconductor Physics  
Sept.2018 – Present
- M.Sc in Radiophysics (Cum Laude)  
Department of Semiconductor Electronics  
Sept. 2016 – June 2018
- B.Sc in Radiophysics  
Department of Semiconductor Electronics  
Sept. 2012 – June 2016

### National Taiwan University (NTU)

QS Global World Ranking #=72

- Exchange student  
Graduate Institute of Electrical  
Engineering and Computer Science  
Sept. 2017 – Jan. 2018

## WORK EXPERIENCE

### Tomsk State University (TSU)

- Laboratory assistant in the scientific  
center «Nanoelectronics»  
Sept.2015 – Jan. 2018
  - Engineer in the scientific  
center «Nanoelectronics»  
Jan.2018 - Present
1. Admittance spectroscopy
  2. Raman spectroscopy
  3. Automation of measuring equipment
  4. Atomic force microscope

## PARTICIPATION IN SCIENTIFIC PROJECTS

- Quantum-dimensional light-emitting diode heterostructure InGaN/GaN/ Al<sub>2</sub>O<sub>3</sub> in the visible wavelength range with short-period superlattices (17.07.2014 — 31.12.2016).
- Development of GaAs sensors for matrix X-ray detectors used in digital mammography and macromolecular crystallography (17.09.2014 — 31.12.2016).
- Research and development of manufacturing technology for ultrahigh-frequency monolithic integrated circuits based on InAlN/GaN heterostructures for space applications (26.09.2017 — present).

## PUBLICATIONS

- Brudnyi V.N., Bojko V.M., Kolin N.G., Kosobutsky A.V., Korulin A.V., Brudnyi P.A., Ermakov V.S. Neutron irradiation-induced modification of electrical and structural properties of GaN epilayers grown on Al<sub>2</sub>O<sub>3</sub> (0001) substrate // Semiconductor Science and Technology. 2018. Vol. 33, № 9. P. 095011-1-095011-8.
- Brudnyi, V.N., Vilisova, M.D., Velikovskii, L.É., Sim, P.E., Brudnyi, P.A. Electrophysical and Physical-Chemical Properties of Ohmic Contacts to III-N Compounds // Russian Physics Journal 61(8).2018. pp. 1450-1456.
- Denis V. Grigoryev, Vadim A. Novikov, Pavel A. Brudnyi, Anna M. Bogatyreva, Victor F. Tarasenko, Michail A. Shulepov. The influence of pulsed volume nanosecond discharge in air at atmospheric pressure on the surface potential distribution of MIS-structures based on p-CdHgTe in the V-defect region // International Congress on Energy Fluxes and Radiation Effects: Abstracts. Tomsk: TPU Publishing House, 2016. P. 272.

## ADDITIONAL INFORMATION

- Languages: Russian – native; English – B2 (IELTS Academic 6.5 - 02.03.2019 )
- Computer literacy (Microsoft Office...)
- Work with graphs and arrays of data (Origin, Mathcad)
- Basics of programming (LabVIEW, Pascal, C++)
- Certificate of first aid courses
- Driving License (Category A, B)
- TSU scholarship for exchange program
- PADI rescue diver certificate